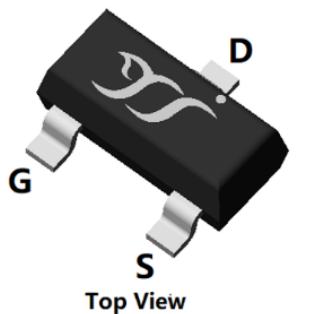
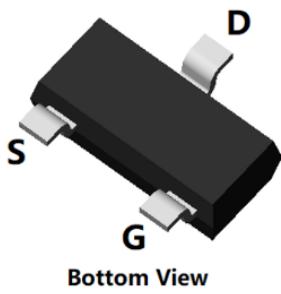


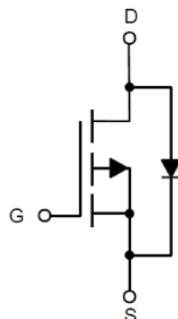
## P-Channel Enhancement Mode Field Effect Transistor



Top View



Bottom View

**SOT-23**

### Product Summary

- $V_{DS}$  -30V
- $I_D$  -4.4A
- $R_{DS(ON)}$  (at  $V_{GS}=-10V$ ) <55mohm
- $R_{DS(ON)}$  (at  $V_{GS}=-4.5V$ ) <68mohm
- $R_{DS(ON)}$  (at  $V_{GS}=-2.5V$ ) <96mohm

### General Description

- Trench Power LV MOSFET technology
- High density cell design for Low  $R_{DS(ON)}$
- High Speed switching
- Part no. with suffix "Q" means AEC-Q101 qualified

### Applications

- Battery protection
- Power management
- Load switch
- 12V Automotive systems

### ■ Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-source Voltage	$V_{DS}$	-30	V
Gate-source Voltage	$V_{GS}$	$\pm 12$	V
Drain Current	$I_D$	-4.4	A
$T_A=125^\circ C$		-1.9	
Pulsed Drain Current <sup>A</sup>	$I_{DM}$	-27	A
Total Power Dissipation	$P_D$	1.2	W
$T_A=125^\circ C$		0.2	W
Thermal Resistance Junction-to-Ambient <sup>B</sup>	$R_{\theta JA}$	104	$^\circ C/W$
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55~+150	$^\circ C$

### ■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJL3401AQ	F2	3401.	3000	30000	120000	7" reel

■ Electrical Characteristics ( $T_J=25^\circ\text{C}$  unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Static Parameter</b>						
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=-250\mu\text{A}$	-30			V
Zero Gate Voltage Drain Current	$I_{\text{DSS}}$	$V_{\text{DS}}=-20\text{V}, V_{\text{GS}}=0\text{V}$			-1	$\mu\text{A}$
Gate-Body Leakage Current	$I_{\text{GSS}}$	$V_{\text{GS}}=\pm 10\text{V}, V_{\text{DS}}=0\text{V}$			$\pm 100$	nA
Gate Threshold Voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=-250\mu\text{A}$	-0.6	-0.9	-1.4	V
Static Drain-Source On-Resistance	$R_{\text{DS(ON)}}$	$V_{\text{GS}}=-10\text{V}, I_{\text{D}}=-4.4\text{A}$		45.5	55	$\text{m}\Omega$
		$V_{\text{GS}}=-4.5\text{V}, I_{\text{D}}=-4\text{A}$		52	68	
		$V_{\text{GS}}=-2.5\text{V}, I_{\text{D}}=-2\text{A}$		64	96	
Diode Forward Voltage	$V_{\text{SD}}$	$I_{\text{S}}=-4.4\text{A}, V_{\text{GS}}=0\text{V}$			-1.2	V
<b>Dynamic Parameters</b>						
Input Capacitance	$C_{\text{iss}}$	$V_{\text{DS}}=-15\text{V}, V_{\text{GS}}=0\text{V}, f=1\text{MHz}$		1040		$\text{pF}$
Output Capacitance	$C_{\text{oss}}$			80		
Reverse Transfer Capacitance	$C_{\text{rss}}$			68		
<b>Switching Parameters</b>						
Total Gate Charge	$Q_g$	$V_{\text{GS}}=-10\text{V}, V_{\text{DS}}=-15\text{V}, I_{\text{D}}=-4.4\text{A}$		18		$\text{nC}$
Gate-Source Charge	$Q_{\text{gs}}$			2.85		
Gate-Drain Charge	$Q_{\text{gd}}$			1.5		
Turn-on Delay Time	$t_{\text{D(on)}}$	$V_{\text{GS}}=-10\text{V}, V_{\text{DS}}=-15\text{V}, I_{\text{D}}=-4.4\text{A}$ $R_{\text{GEN}}=3\Omega$		5.0		$\text{ns}$
Turn-on Rise Time	$t_r$			30		
Turn-off Delay Time	$t_{\text{D(off)}}$			29		
Turn-off fall Time	$t_f$			48		

- A. Repetitive rating; pulse width limited by max. junction temperature.  
 B. The value of  $R_{\theta,\text{JA}}$  is measured with the device mounted on the minimum recommend pad size, in the still air environment with  $T_A = 25^\circ\text{C}$ . The maximum allowed junction temperature of  $150^\circ\text{C}$ . The value in any given application depends on the user's specific board design.

\*

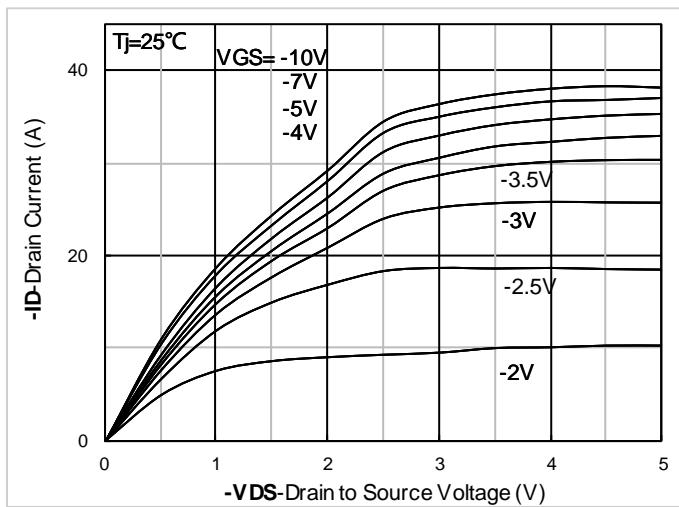
**■ Typical Performance Characteristics**

Figure1. Output Characteristics

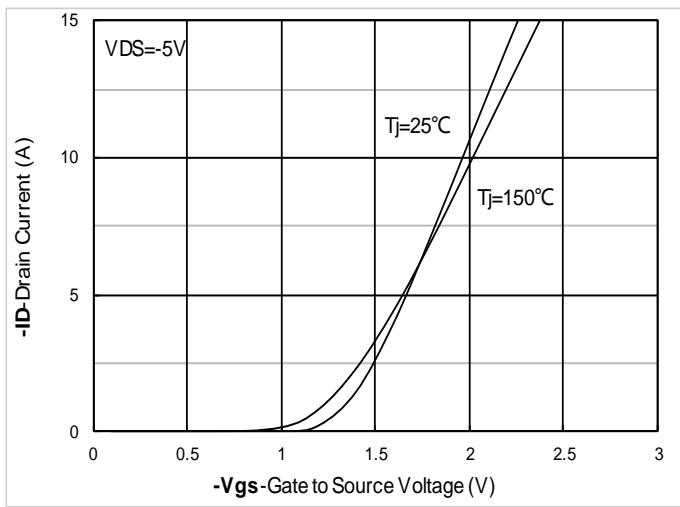


Figure2. Transfer Characteristics

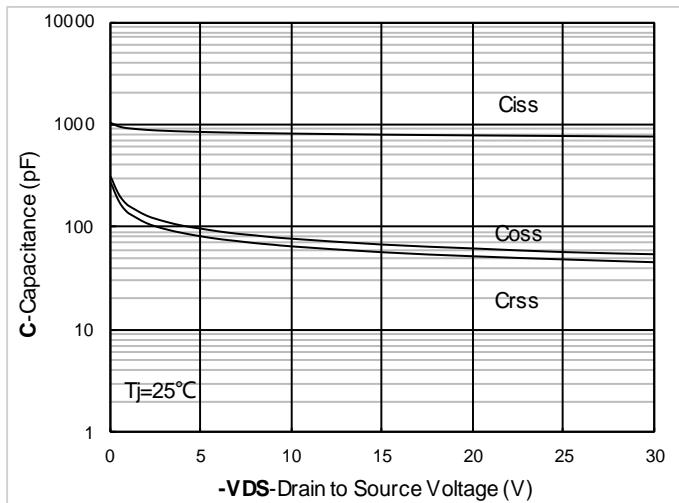


Figure3. Capacitance Characteristics

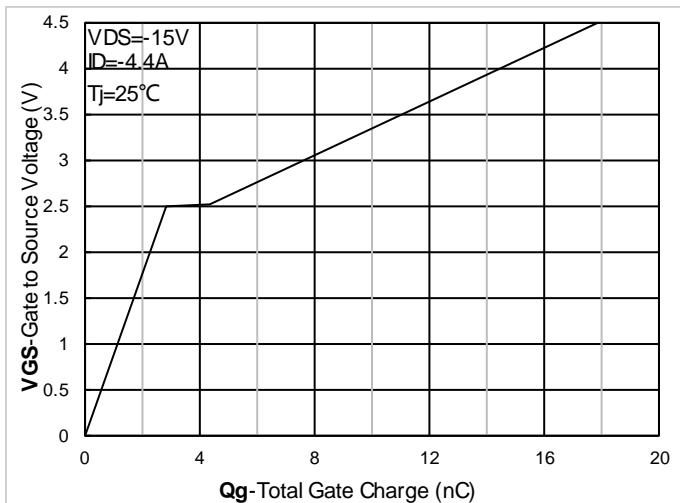


Figure4. Gate Charge

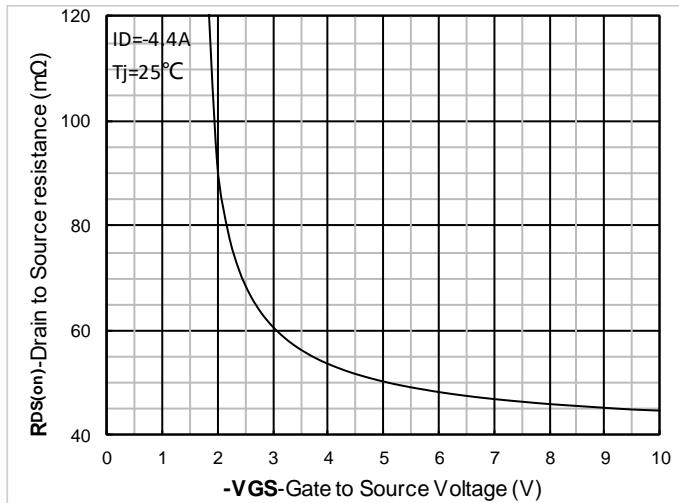


Figure5. On-Resistance vs Gate to Source Voltage

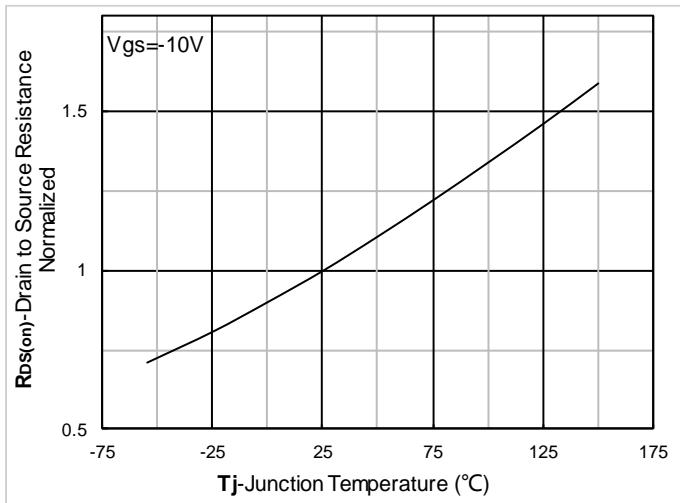


Figure6. Normalized On-Resistance

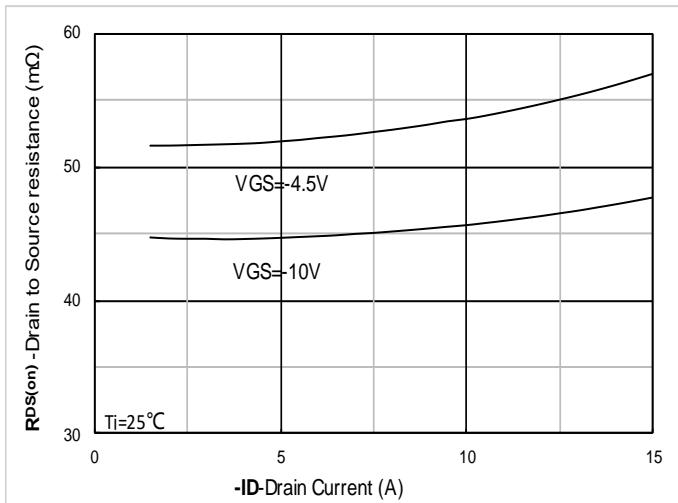
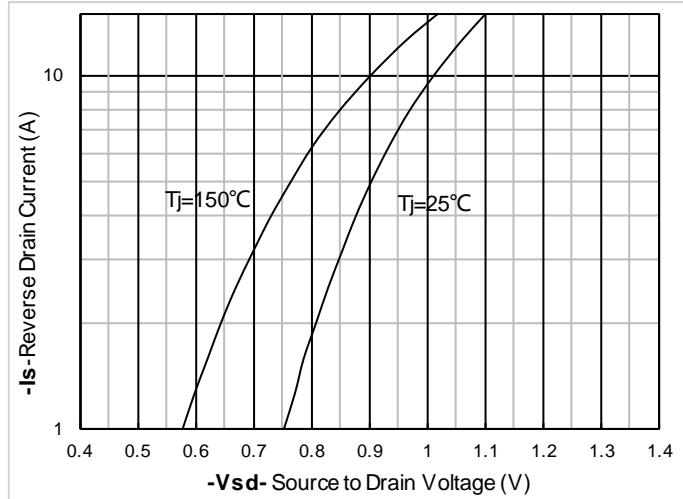
Figure 7.  $R_{DS(on)}$  VS Drain Current

Figure 8. Forward characteristics of reverse diode

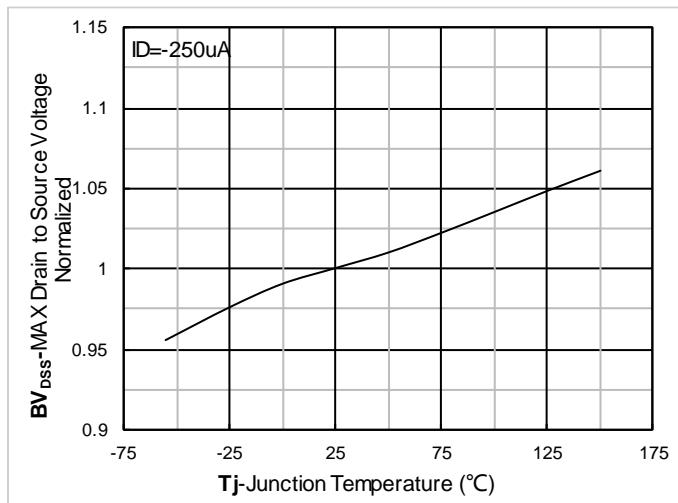


Figure 9. Normalized breakdown voltage

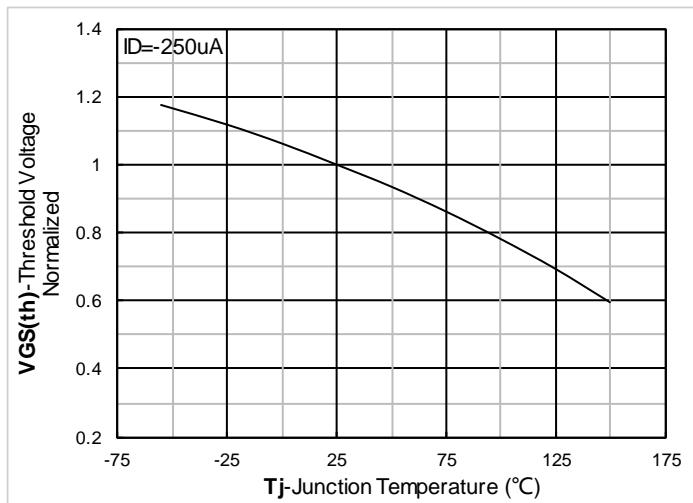


Figure 10. Normalized Threshold voltage

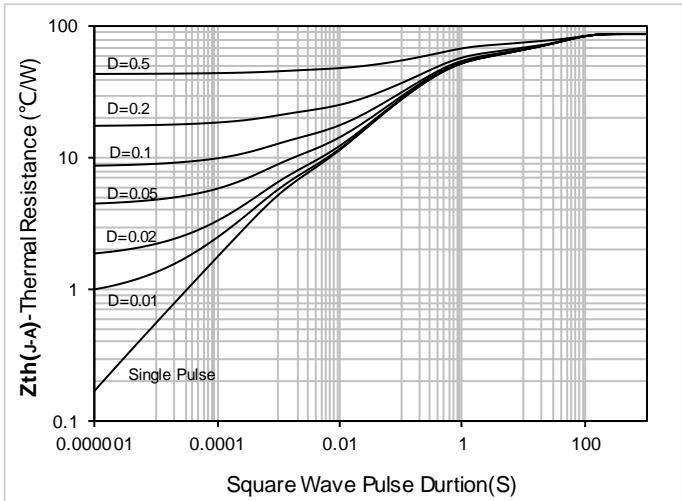


Figure 11. Maximum Transient Thermal Impedance

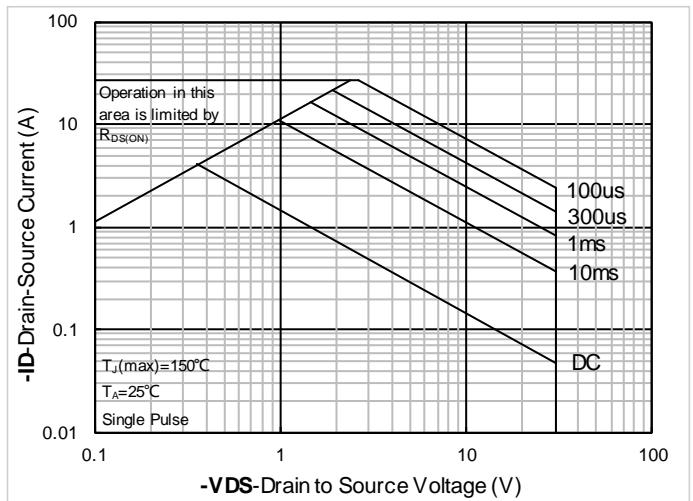
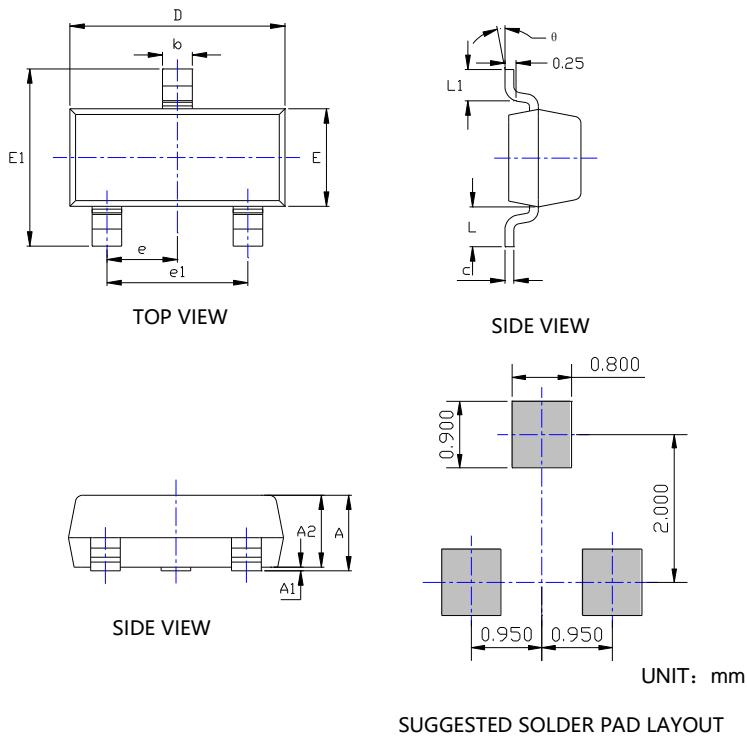


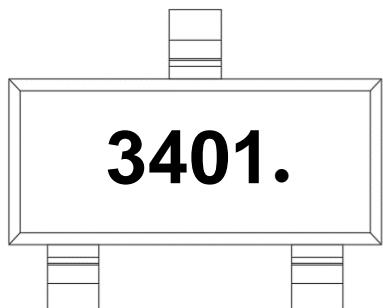
Figure 12. Safe Operation Area

**■ SOT-23 Package information**

SYMBOL	DIMENSIONS			
	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.035	0.045	0.900	1.150
A1	0.000	0.004	0.000	0.100
A2	0.035	0.041	0.900	1.050
b	0.012	0.020	0.300	0.500
c	0.004	0.008	0.100	0.200
D	0.110	0.118	2.800	3.000
E	0.047	0.055	1.200	1.400
E1	0.089	0.100	2.250	2.550
e	0.037TYP		0.950TYP	
e1	0.071	0.079	1.800	2.000
L	0.022REF		0.550REF	
L1	0.012	0.020	0.300	0.500
θ	0°	8°	0°	8°

## NOTE:

1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
2. TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
3. THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.

**■ Marking Information**

## Note:

1. All marking is at middle of the product body
2. All marking is in laser marking
3. 3401 is Marking Code
4. Body color: Black



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